

### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	20 -20		V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 10 <u>+</u> 10		V
Continuous Drain Current		I <sub>D</sub>	0.5	-0.5	А
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	1.0	-1.0	А
Power Dissipation	T <sub>a</sub> =25°C		300		mW
	Derate above 25°C	P <sub>D</sub>	2.4		mW/°C
Operating Junction and Storage Ten	$T_J, T_STG$	-55~150		°C	
Typical Thermal Resistance - Junction to Ambient <sup>(Note 3)</sup>		R <sub>eja</sub>	417		°C/W



### N-Channel Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> = 250uA	20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}, I_{D}=250uA$	0.3	0.64	0.9	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ = 4.5V, I <sub>D</sub> = 500mA	-	0.31	0.4	Ω
		$V_{GS}$ = 2.5V, I <sub>D</sub> = 200mA	-	0.36	0.65	
		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 100mA	-	0.43	0.8	
		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 50mA	-	0.51	1.2	
		V <sub>GS</sub> = 1.2V, I <sub>D</sub> = 20mA	-	0.71	3.0	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 16V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	<u>+</u> 0.5	<u>+</u> 10	uA
Dynamic (Note 5)						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V, I <sub>D</sub> =500mA, V <sub>GS</sub> =4.5V	-	1.4	-	nC
Gate-Source Charge	$Q_gs$		-	0.22	-	
Gate-Drain Charge	$Q_gd$		-	0.21	-	
Input Capacitance	Ciss		-	67	-	pF
Output Capacitance	Coss	$V_{DS}$ =10V, $V_{GS}$ =0V,	-	19	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	6	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	2.8	-	ns
Turn-On Rise Time	tr	$V_{DD}$ =10V, I <sub>D</sub> =150mA, $V_{GS}$ =4V, $R_{G}$ =10 $\Omega$ <sup>(Note 1,2)</sup>	-	20	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	23	-	
Turn-Off Fall Time	tf	$R_{G}=10\Omega$	-	23	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	Is		-		500	mA
Diode Forward Current	IS				500	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = 500mA, V <sub>GS</sub> =0V	-	0.87	1.3	V

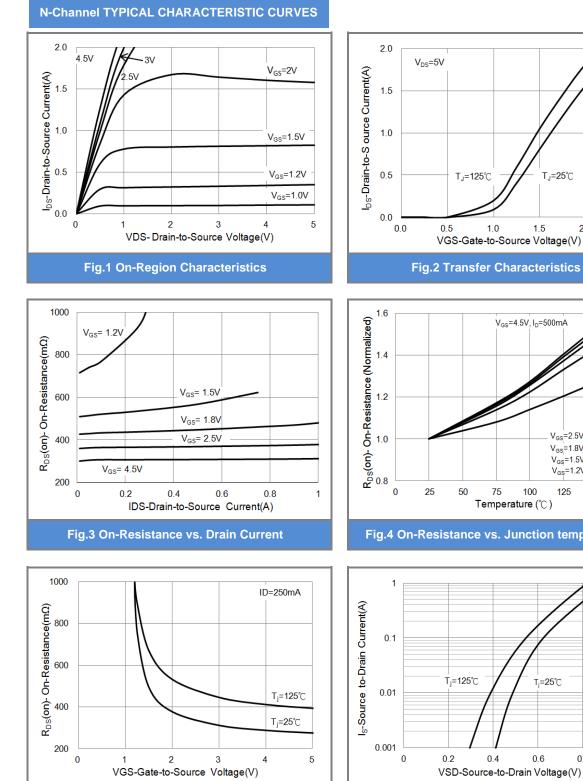


### P-Channel Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static				-	-	-
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V,I_{D}=-250uA$	-20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250$ uA	-0.3	-0.6	-1.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-500mA	-	0.9	1.2	Ω
		V <sub>GS</sub> =-2.5V,I <sub>D</sub> =-200mA	-	1.07	1.5	
		V <sub>GS</sub> =-1.8V,I <sub>D</sub> =-100mA	-	1.25	2.2	
		V <sub>GS</sub> =-1.5V,I <sub>D</sub> =-40mA	-	1.42	3.6	
		V <sub>GS</sub> =-1.2V,I <sub>D</sub> =-10mA	-	1.7	6.0	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-16V,V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V,V <sub>DS</sub> =0V	-	<u>+</u> 2	<u>+</u> 10	uA
Dynamic (Note 5)						
Total Gate Charge	$Q_g$	- V <sub>DS</sub> =-10V, I <sub>D</sub> =-500mA, - V <sub>GS</sub> =-4.5V	-	1.4	-	nC
Gate-Source Charge	$Q_gs$		-	0.19	-	
Gate-Drain Charge	$Q_gd$		-	0.2	-	
Input Capacitance	Ciss		-	38	-	pF
Output Capacitance	Coss	$V_{DS}$ =-10V, $V_{GS}$ =0V,	-	15	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	9	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	7.2	-	ns
Turn-On Rise Time	tr	$V_{DD}$ =-10V, $I_{D}$ =-500mA,	-	21	-	
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}$ =-4.5V, R <sub>G</sub> =6 $\Omega^{(Note 1,2)}$	-	85	-	
Turn-Off Fall Time	tf	K <sub>G</sub> =017	-	116	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					500	mA
Diode Forward Current	I <sub>S</sub>		-	-	-500	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-500mA, V <sub>GS</sub> =0V	-	-0.9	-1.3	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. RoJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.



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Fig.5 On-Resistance Variation with VGS.



**Fig.6 Body Diode Characteristics** 

T\_**=25℃** 

2.0

V<sub>GS</sub>=2.5V, I<sub>D</sub>=200mA

V<sub>GS</sub>=1.8V, I<sub>D</sub>=100mA V<sub>GS</sub>=1.5V, I<sub>D</sub>=50mA

V<sub>GS</sub>=1.2V, I<sub>D</sub>=20mA

0.8

1

150

175

125

2.5



### N-Channel TYPICAL CHARACTERISTIC CURVES

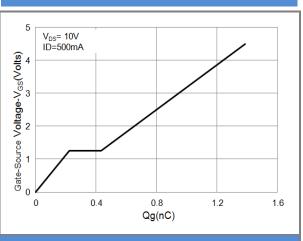


Fig.7 Gate-Charge Characteristics

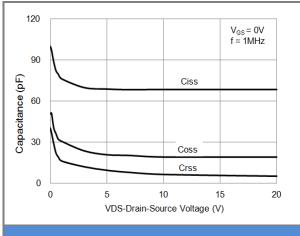
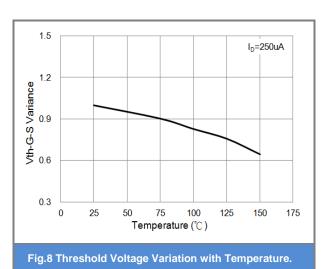


Fig.9 Capacitance vs. Drain-Source Voltage.



#### PJX8601 P-Channel TYPICAL CHARACTERISTIC CURVES 1.0 1.00 V<sub>DS</sub>=-5V -4.5V -I<sub>DS</sub>-Drain-to-S ource Current(A) <sub>ss</sub>=-3∨ -I<sub>DS</sub>-Drain-to-Source Current(A) 70 80 80 80 80 80 0.75 V<sub>GS</sub>=-2V V<sub>GS</sub>=-1.5V 0.50 V<sub>GS</sub>=-1.2V 0.25 V<sub>GS</sub>=-1V T\_**=125℃** T\_**=25℃** 0.00 0 2 5 1 3 4 0.0 0.5 1.0 1.5 2.0 2.5 -V<sub>DS</sub>- Drain-to-Source Voltage(V) -V<sub>GS</sub>-Gate-to-Source Voltage(V) **Fig.1 On-Region Characteristics Fig.2 Transfer Characteristics** 3.0 1.6 R<sub>Ds</sub>(on)- On-Resistance (Normalized) V<sub>GS</sub>= -1.2V $R_{DS}(on)$ - On-Resistance( $\Omega$ ) 2.5 V<sub>GS</sub>=-4.5V, I<sub>D</sub>=-500mA 1.4 V<sub>GS</sub>= -1.5V 2.0 1.2 V<sub>GS</sub>= -1.8V 1.5 V<sub>GS</sub>=-2.5V, I<sub>D</sub>=-200mA V<sub>GS</sub>= -2.5V V<sub>GS</sub>=-1.8V, I<sub>D</sub>=-100mA 1.0 V<sub>GS</sub>= -4.5V V<sub>GS</sub>=-1.5V, I<sub>D</sub>=-50mA 1.0 V<sub>GS</sub>=-1.8V, I<sub>D</sub>=-10mA 0.8 0.5 0 25 75 100 125 150 175 50 0.0 0.2 0.4 0.6 0.8 Temperature (℃) -I<sub>DS</sub>-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 1 2.5 ID=-250mA -Is-Source to-Drain Current(A) $R_{DS}(on)$ - On-Resistance( $\Omega$ ) 2.0 0.1 1.5 Tj=125℃ . Tj=125℃ T<sub>i</sub>=25℃ 0.01 T<sub>i</sub>=25℃ 1.0 0.5 0.001 0 3 5 1 2 4 0 0.2 0.4 0.6 0.8 1 -V<sub>GS</sub>-Gate-to-Source Voltage(V) -V<sub>SD</sub>-Source-to-Drain voltage(V)

Fig.5 On-Resistance Variation with VGS.



**Fig.6 Body Diode Characteristics** 

### P-Channel TYPICAL CHARACTERISTIC CURVES

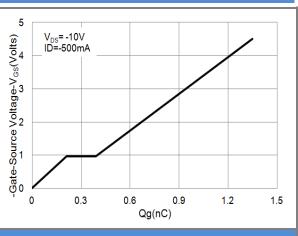


Fig.7 Gate-Charge Characteristics

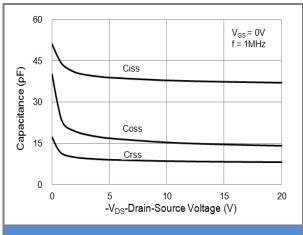
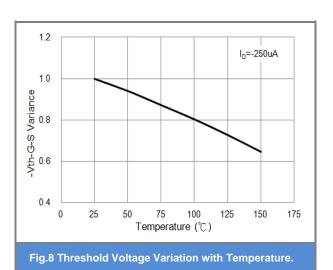


Fig.9 Threshold Voltage Variation with Temperature.

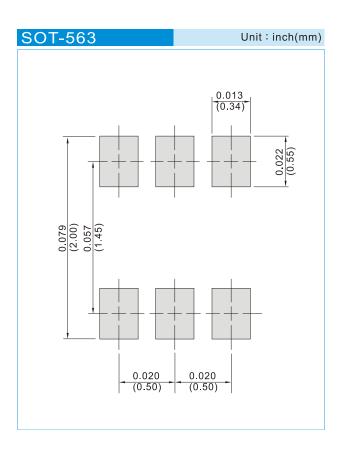




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJX8601_R1_00001	SOT-563	4K pcs / 7" reel	X61	Halogen free

### **MOUNTING PAD LAYOUT**





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